IN THE CLAIMS

Please amend the claims as follows:

1. (Previously presented) A method of fabricating an energy storage device, comprising:

providing a substrate;

forming an electrode first film on the substrate;

forming an electrolyte second film on the first film, wherein forming the electrolyte second film includes:

depositing electrolyte material using a deposition source; and

supplying energized particles from a second source such that the particles provide energy to the electrolyte material to deposit the electrolyte material into a desired film structure; and

forming an electrode third film on the second film.

2. (Original) The method of claim 1, wherein supplying energized particles includes supplying ions having an energy of greater than about 5 eV.

3. (Original) The method of claim 1, wherein supplying energized particles includes supplying ions having an energy of less than about 3000 eV.

4. (Original) The method of claim 1, wherein supplying energized particles includes supplying ions having an energy in the range of about 5 eV to about 500 eV.

5. (Original) The method of claim 1, wherein supplying energized particles includes supplying ions having an energy in the range of about 5 eV to about 250 eV.

6. (Original) The method of claim 1, wherein supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 200 eV.

7. (Original) The method of claim 1, wherein supplying energized particles includes supplying ions having an energy in the range of about 0 eV to about 40 eV.

8. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 5000 Angstroms.

9. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 2500 Angstroms.

10. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 1000 Angstroms.

11. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 500 Angstroms.

12. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 250 Angstroms.

13. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 100 Angstroms.

14. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness in a range of about 10 Angstroms to about 200 Angstroms.

15. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness in a range of about 10 Angstroms to about 100 Angstroms.

16. (Original) The method of claim 1, wherein depositing electrolyte material includes depositing Li_3PO_4 electrolyte material.

17. (Original) The method of claim 1, wherein supplying energized particles includes supplying energized nitrogen particles, and reacting the nitrogen particles with the Li_3PO_4 electrolyte material.

18. (Original) The method of claim 1, wherein forming the electrolyte second film includes providing a nitrogen-enriched atmosphere in which the Li_3PO_4 electrolyte material is deposited.

19. (Original) The method of claim 1, wherein forming the electrolyte film includes forming the electrolyte film to a thickness sufficient to insulate the electrode first film from the electrode second film and to allow ion transport between the electrode first film and the electrode second film.

20. (Original) The method of claim 19, wherein forming the electrode first film includes depositing at least one of a metal and an intercalation material.

21. (Original) The method of claim 20, wherein forming the electrode third film includes depositing at least one of a metal and an intercalation material.

22. (Original) The method of claim 1, wherein forming the electrolyte second film includes forming the electrolyte film to a thickness in a range of about 1 nanometer to about 250 nanometers.

23. (Original) The method of any of claims 1 through 22, wherein the electrolyte second film is lithium phosphorus oxynitride.

24. (Original) The method of any of claims 1 through 22, wherein the electrolyte second film is a silicon dioxide.

25. (Original) The method of any of claims 1 through 22, wherein the electrolyte second film is an aluminum oxide.

26-36. (Cancelled)

37. (Previously presented) An apparatus comprising:

a substrate;

means forming an electrode first film on the substrate;

means for forming an electrolyte second film on the first film, wherein the means for forming the electrolyte second film includes:

means for depositing electrolyte material using a deposition source; and

means for supplying energized particles from a second source such that the particles provide energy to the electrolyte material to deposit the electrolyte material into a desired film structure; and

means for forming an electrode third film on the second film.

38. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 5 eV to about 50 eV.

39. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 5 eV to about 40 eV.

40. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 5 eV to about 30 eV.

41. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 5 eV to about 20 eV.

42. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 500 eV.

43. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 400 eV.

44. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 300 eV.

45. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 250 eV.

46. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 200 eV.

47. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 150 eV.

48. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 100 eV.

49. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 50 eV.

50. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 40 eV.

51. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 30 eV.

52. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 10 eV to about 20 eV.

53. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 300 eV.

54. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 250 eV.

55. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 200 eV.

56. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 150 eV.

57. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 100 eV.

58. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 50 eV.

59. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 40 eV.

60. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20eV to about 30 eV.

61. (New) The method of claim 1, wherein the supplying energized particles includes supplying ions having an energy in the range of about 20 eV.

62. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than 5000 Angstroms.

63. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than 4000 Angstroms.

64. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than 3000 Angstroms.

65. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than 2000 Angstroms.

66. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than 1000 Angstroms.

67. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than 500 Angstroms.

68. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 400 Angstroms.

69. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 300 Angstroms.

70. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 250 Angstroms.

71. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 200 Angstroms.

72. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 150 Angstroms.

73. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 100 Angstroms.

74. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 75 Angstroms.

75. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 50 Angstroms.

76. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 30 Angstroms.

77. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of less than about 20 Angstroms.

78. (New) The method of claim 1, wherein the forming the electrolyte second film includes forming the electrolyte film to a thickness of about 20 Angstroms.

79. (New) The method of claim 1, wherein the, forming the electrolyte second film includes forming the electrolyte film to a thickness of about 10 Angstroms.

80. (New) The method of claim 1, wherein the forming of the first film includes depositing a vanadium oxide, the forming of the second film includes depositing lithium phosphorus oxynitride, and the forming of the third film includes depositing a lithium intercalation material.

81. (New) The method of claim 1, wherein the forming of the electrode first film includes depositing an intercalation material.

82. (New) The method of claim 81, wherein the forming of the electrode third film includes depositing a metal.

83. (New) The method of claim 1, wherein the forming of the electrode first film includes depositing a metal.

84. (New) The method of claim 83, wherein the forming of the electrode third film includes depositing an intercalation material.